

**4.0A 4Quadrants TRIACs**

**Product Summary**

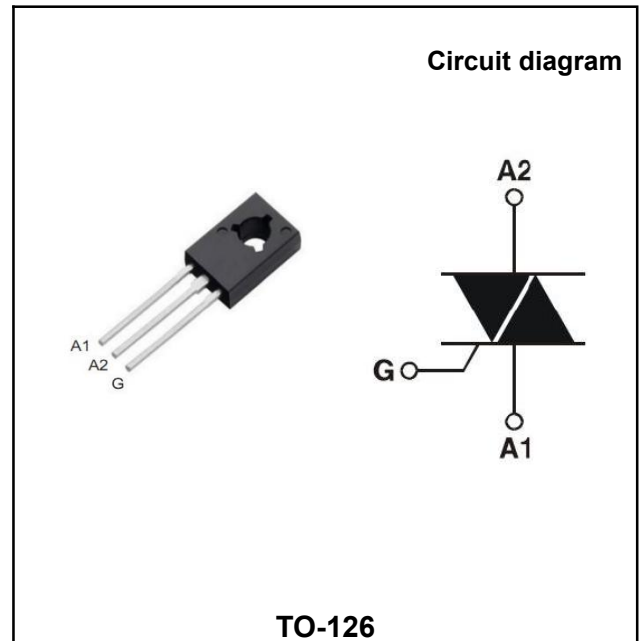
Symbol	Value	Unit
$I_{T(RMS)}$	4.0	A
$V_{DRM} V_{RRM}$	600/800	V
$V_{TM}$	1.55	V

**Features**

With high ability to withstand the shock loading of large current, With high commutation performances, 4 quadrants products especially recommended for use on inductive load.

**Application**

Washing machine, vacuums, massager, solid state relay, AC Motor speed regulation and so on.



**Order Information**

Part Number	Package	Marking	Packing	Packing Quantity
BT134	TO-126	BT134 XXXX	Box	500PCS/Box

**Absolute maximum ratings (Ta=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit	
Repetitive peak off-state voltage	$V_{DRM}$	600/800	V	
Repetitive peak reverse voltage	$V_{RRM}$	600/800	V	
RMS on-state current	$I_{T(RMS)}$	4	A	
Non repetitive surge peak on-state current (full cycle, F=50Hz)	$I_{TSM}$	25	A	
I <sup>2</sup> t value for fusing (tp=10ms)	I <sup>2</sup> t	3.1	A <sup>2</sup> s	
Critical rate of rise of on-state current (I <sub>G</sub> = 2 x I <sub>GT</sub> )	$di_T/dt$	I - II - III	50	A/us
		IV	10	A/us
Peak gate current	$I_{GM}$	2	A	
Average gate power dissipation	$P_G (AV)$	0.5	W	
Junction Temperature	$T_J$	-40~+125	°C	
Storage Temperature	$T_{STG}$	-40 ~+150	°C	

**Electrical characteristics (TA=25°C, unless otherwise noted)**

Parameter	Symbol	Test Condition	Value		Unit	
			Min	Max		
Gate trigger current	$I_{GT}$	$V_D=12V$ $I_T=0.1A$ $T_j=25^\circ C$	I-II-III	-	10	<b>mA</b>
			IV	-	25	
Gate trigger voltage	$V_{GT}$	I-II-III-IV	-	1.3	<b>V</b>	
Gate non-trigger voltage	$V_{GD}$	$V_D = V_{DRM}$ $T_j=125^\circ C$	0.2	-	<b>V</b>	
latching current	$I_L$	$V_D = 12V$ $I_{GT}=0.1A$ $T_j=25^\circ C$	I-III-IV	-	15	<b>mA</b>
			II	-	20	
Holding current	$I_H$	I-II-III-IV	-	15	<b>mA</b>	
Critical-rate of rise of commutation voltage	$dV_D/dt$	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ C$	20	-	<b>V/us</b>	

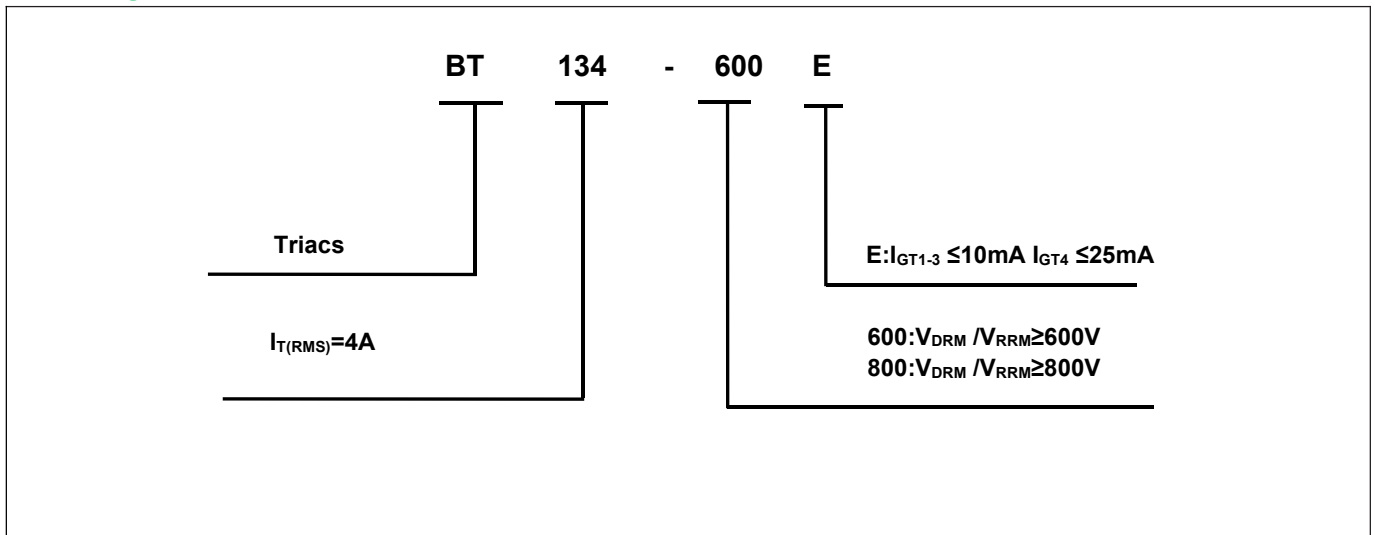
**STATIC CHARACTERISTICS**

Forward "on" voltage	$V_{TM}$	$I_{TM} = 6A$ $t_p=380us$	-	1.55	<b>V</b>	
Repetitive Peak Off-State Current	$I_{DRM}$	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ C$	-	5	<b>uA</b>
Repetitive Peak Reverse Current	$I_{RRM}$		$T_j=125^\circ C$	-	500	<b>uA</b>

**THERMAL RESISTANCES**

Thermal resistance	$R_{th(j-c)}$	Junction to case(AC)	TYP.	3	<b>°C/W</b>
	$R_{th(j-a)}$	Junction to ambient	TYP.	100	<b>°C/W</b>

**Ordering Information**



Typical Characteristics

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

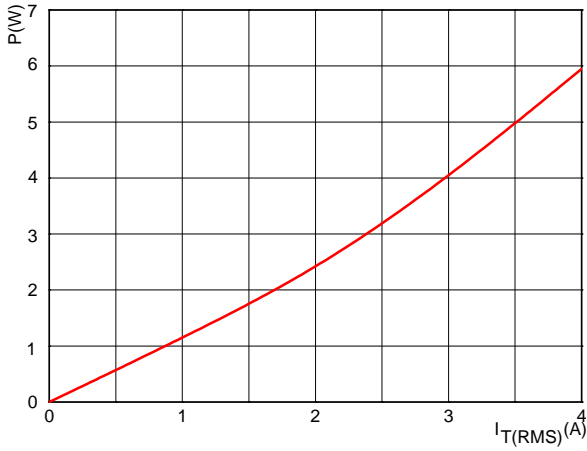


FIG.2: RMS on-state current versus case temperature (full cycle)

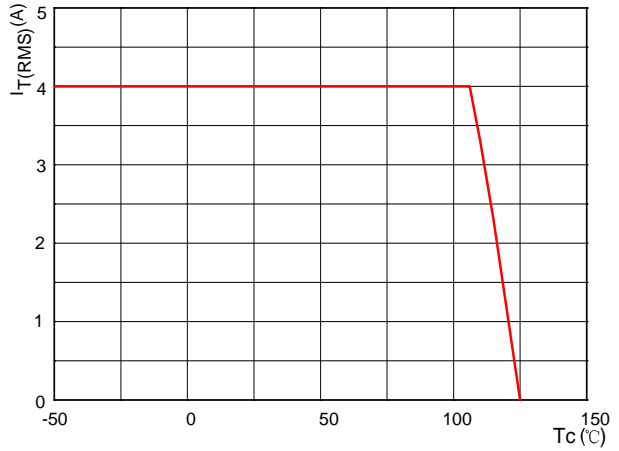


FIG.3: Surge peak on-state current versus number of cycles

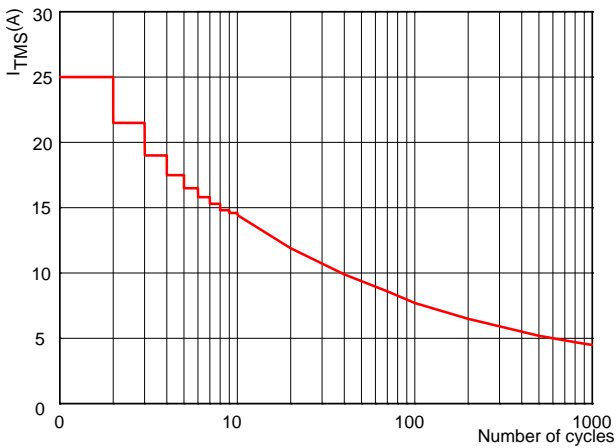


FIG.4: On-state characteristics (maximum values)

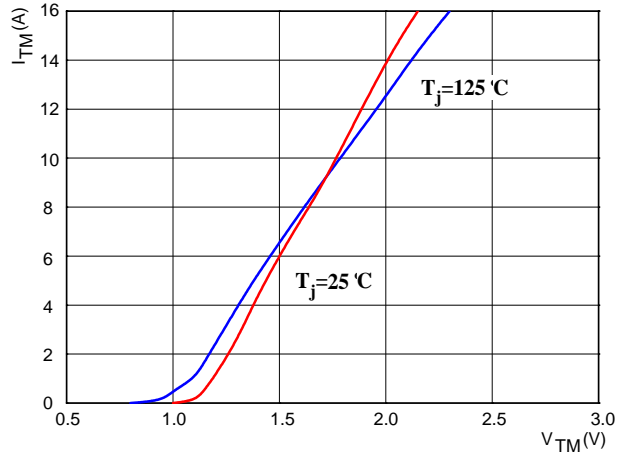


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ms}$

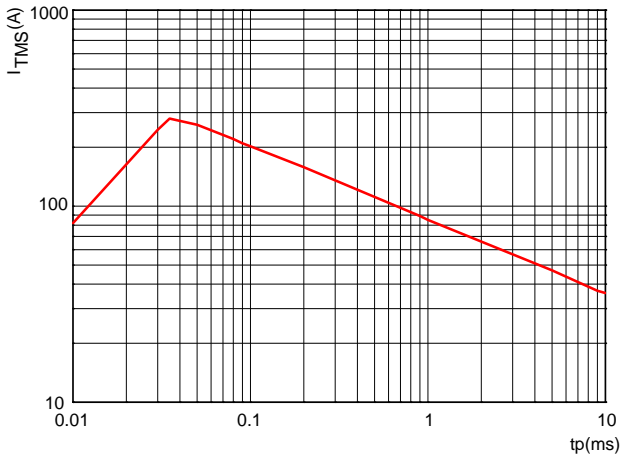
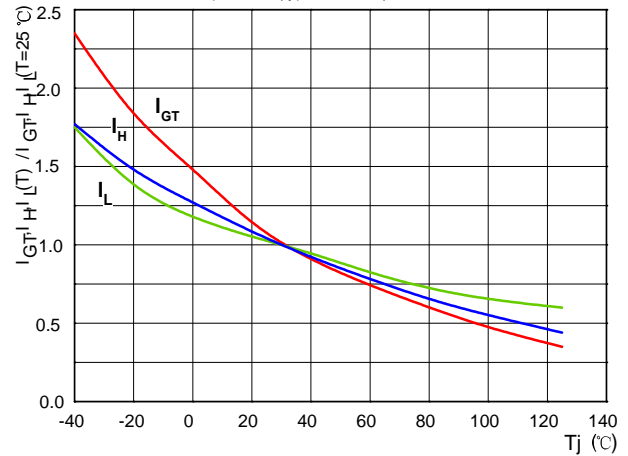


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



TO-126

